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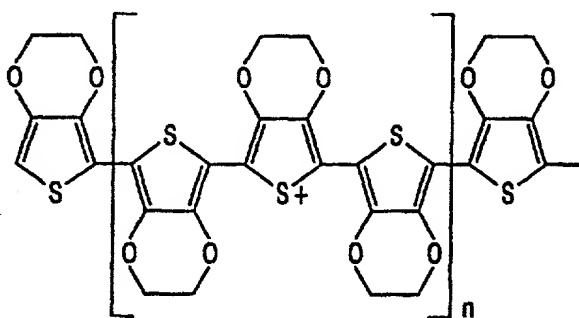
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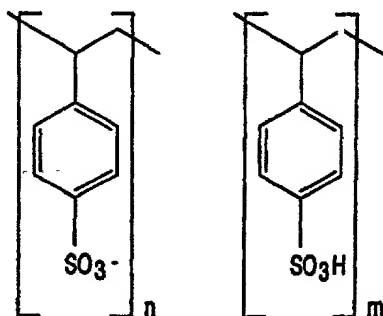
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(54) Title: CONDUCTIVE STRUCTURE BASED ON POLY-3,4-ALKENEDIOXYTHIOPHENE (PEDOT) AND POLYSTYRE-
NESULFONIC ACID (PSS)



(57) Abstract: An electronic component has an electrically con-
ductive relief structure (3) which contains a salt of a poly-3,4-
alkylenedioxythiophene. This salt provides the structure with a
stable conductivity. The salt is a polyacid salt by preference. The
polyacid salt of poly-3,4-alkylenedioxythiophene is used in the
method of manufacturing a relief structure on an electrically in-
sulating substrate. Relief structures (3) comprising tracks (311-
314, 321-324) and channels (141) with track widths (tW) and
channel lengths (cL) of less than 10 µm can be achieved. The
tracks (311-314; 321-324) are used as electrodes (31; 32), the
channels (141) are used as semiconductor channels in electronic
components, especially in fieldeffect transistors (11) and light-
emitting diodes.



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